

What is claimed is:

1. An electron beam recording substrate where electron beam information recording is carried out comprising: a substrate main body; a resist film relative to the substrate main body; and a surface layer area made of a material that suppresses enlargement of a scattering distribution diameter of electrons spread inside by irradiation of an electron beam from a resist film side.
2. The electron beam recording substrate according to claim 1, wherein the substrate main body is positioned on a side opposite to said resist film with respect to said surface layer area.
3. The electron beam recording substrate according to claim 1, wherein said electron beam recording substrate is made only of a same material as said material for said surface layer area.
4. The electron beam recording substrate according to claim 1, wherein said surface layer area is made of a material containing at least one of elements with atomic numbers 21 to 36, 38 to 54 and 56 to 83 by 50 wt% or greater.
5. The electron beam recording substrate according to claim 1, wherein said surface layer area is made of a material

containing at least one of elements with atomic numbers 73 to 79 by 50 wt% or greater.

6. The electron beam recording substrate according to claim 2, wherein said surface layer area is made of a material containing at least one of elements with atomic numbers 73 to 79 by 50 wt% or greater and said substrate main body is made of a material containing at least one of elements with atomic numbers 13, 14, 21 to 36, 38 to 54, 56, 57, 72 and 80 to 83 by 50 wt% or greater.

7. The electron beam recording substrate according to claim 2, wherein said surface layer area is comprised of a plurality of thin films.

8. The electron beam recording substrate according to claim 6, wherein that thin film in said plurality of thin films which is in contact with said resist film is made of a material containing at least one of elements with atomic numbers 73 to 79 by 50 wt% or greater and those other than said thin film contacting said resist film are made of a material containing at least one of elements with atomic numbers 21 to 36, 38 to 54, 56, 57, 72 and 80 to 83 by 50 wt% or greater.

9. The electron beam recording substrate according to claim 6, wherein that thin film in said plurality of thin films which is in contact with said resist film is made of a material

containing at least one of elements with atomic numbers 21 to 36, 38 to 54, 56, 57, 72 and 80 to 83 by 50 wt% or greater and those other than said thin film contacting said resist film are made of a material containing at least one of elements with atomic numbers 73 to 79 by 50 wt% or greater.